

Temperature and frequency dependences of dielectric properties of sodium sulfate single crystal

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Temperature and frequency dependences of dielectric properties of sodium sulfate single crystal

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The dielectric constant (ϵ') and loss tangent ($\tan\delta$) of sodium sulfate (Na_2SO_4) single crystal, grown at 50°C from aqueous solution, have been determined from room temperature to 250°C at different frequencies between 10^2 Hz and 10^5 Hz and at 10^{10} Hz. The dielectric measurements are taken on the setup described earlier.¹

The variation of ϵ' and $\tan\delta$ with frequency for a single crystal of Na_2SO_4 at five different temperatures is shown in Fig. 1. At room temperature (27°C), there is a very slow decrease in the dielectric constant with the increase of frequency which attains an almost constant value of 5.68 beyond 3 kHz. With the increase of temperature there is an increase in the dielectric constant, which is more prominent in the low frequency region. The variation of $\tan\delta$ with frequency at various temperatures is similar to that of ϵ' . The dependence of ϵ' on temperature at the frequencies 2 kHz, 10 kHz, 100 kHz, and 10 GHz for the same crystal is shown in Fig. 2. The variation of $\tan\delta$ with temperature is also shown in the same figure. No loss is observed at the microwave frequency (10 GHz), the minimum detectable loss being

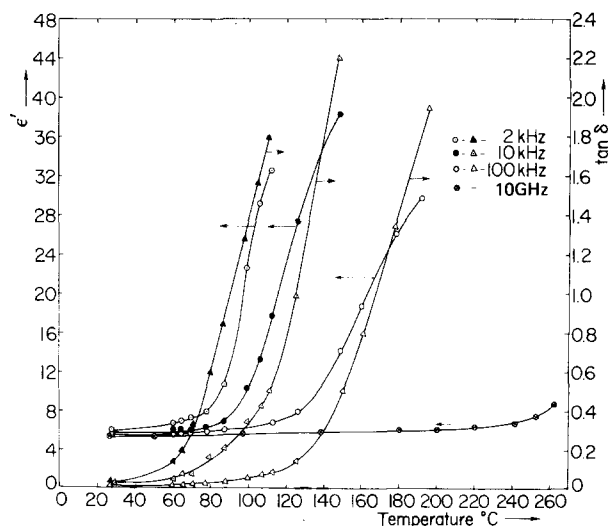


FIG. 2. Temperature variation of dielectric constant and loss tangent of Na_2SO_4 crystal at different frequencies.

0.005.

The dielectric constant of Na_2SO_4 has a positive temperature coefficient at 10 GHz. At low frequen-

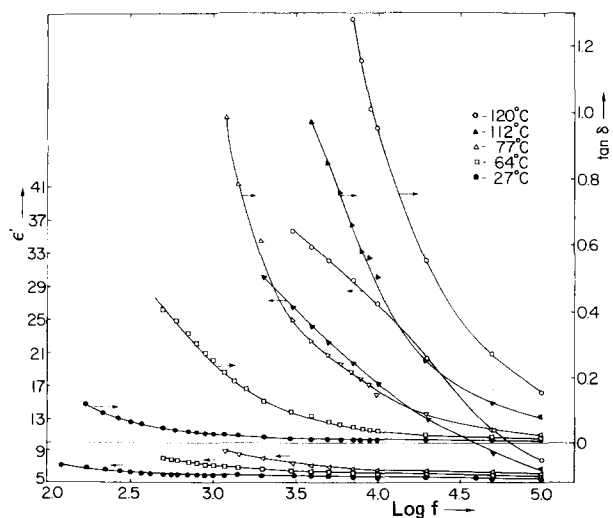


FIG. 1. Variation of dielectric constant and loss tangent of Na_2SO_4 crystal with frequency at different temperatures.

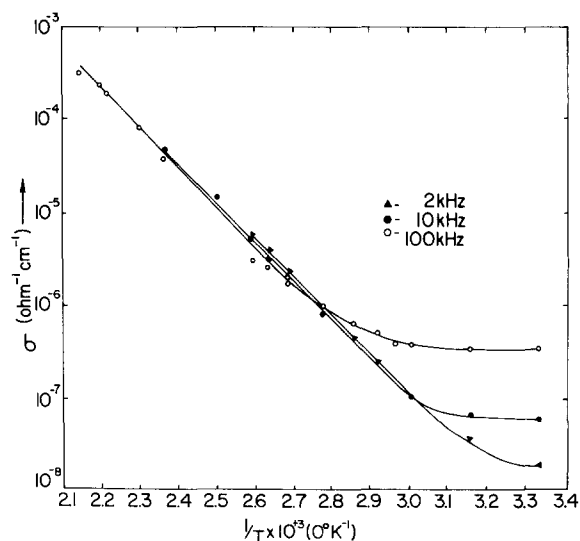


FIG. 3. Dielectric conductivity of Na_2SO_4 crystal at different frequencies.

cies, defects and imperfections cause sharp increases in both ϵ' and $\tan\delta$. Similar results were reported earlier in KTaO_3 ,² calcite crystal,³ and Li_2SO_4 .¹ The large dielectric constant at high temperature indicates less electrostatic binding between ions; therefore, less energy is required to move charge carriers. Rao and Smakula⁴ attributed the high dielectric constant in the high temperature region to the creation and destruction of dipoles.

Using the relation $\epsilon'' = \epsilon' \tan\delta$, the loss factor ϵ'' is obtained and the dielectric conductivity $\sigma = \omega\epsilon_0\epsilon''$ (where ω is angular frequency and ϵ_0 is vacuum dielectric constant) is calculated at different temperatures for different frequencies. A plot of $\log\sigma$ against $1/T$ is shown in Fig. 3 for 2 kHz,

10 kHz, and 100 kHz. The curves have two distinct regions above room temperature. Below 80 °C, the conductivity is strongly frequency dependent and is due to associated defects as well as free charge carriers. Above 80 °C the dielectric conductivity is frequency independent; this intrinsic region has an activation energy of 0.36 eV, about the same as previously reported for $\text{LiSO}_4 \cdot \text{H}_2\text{O}$ (0.34 eV).¹

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